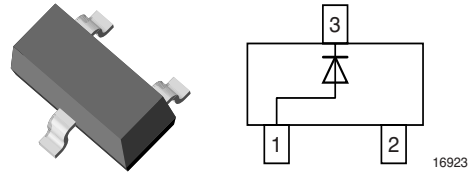


Small Signal Switching Diode

Features

- Silicon Epitaxial Planar Diode
- Fast switching diode in case SOT-23, especially suited for automatic insertion.



Mechanical Data

Case: SOT-23 Plastic case

Weight: approx. 8.8 mg

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Ordering code	Marking	Remarks
MMBD6050	MMBD6050-GS18 or MMBD6050-GS08	5AM	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Continuous reverse voltage		V_R	70	V
Forward current		I_F	200	mA
Peak forward surge current		I_{FSM}	500	mA
Maximum power dissipation on FR-5 board ¹⁾	$T_A = 25\text{ }^{\circ}\text{C}$	P_{tot}	225	mW
	Derate above 25 $^{\circ}\text{C}$	P_{tot}	1.8	mW/ $^{\circ}\text{C}$
Maximum power dissipation on Alumina substrate ²⁾	$T_A = 25\text{ }^{\circ}\text{C}$	P_{tot}	300	mW
	Derate above 25 $^{\circ}\text{C}$	P_{tot}	2.4	mW/ $^{\circ}\text{C}$

¹⁾ FR-5 = 1.0 x 0.75 x 0.062 in.

²⁾ Alumina = 0.4 x 0.3 x 0.024 in. 99.5 % alumina

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance FR-5		R_{thJA}	556	$^{\circ}\text{C}/\text{W}$
Junction to ambient Alumina		R_{thJA}	417	$^{\circ}\text{C}/\text{W}$
Maximum junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_S	- 55 to + 150	$^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	70			V
Forward voltage	$I_F = 1\text{ mA}$	V_F	0.55		0.7	V
	$I_F = 100\text{ mA}$	V_F	0.85		1.1	V
Reverse leakage current	$V_R = 50\text{ V}$	I_R			0.1	μA
Reverse recovery time	$I_F = I_R = 10\text{ mA}$, $I_{rr} = 1\text{ mA}$	t_{rr}			4	ns
Diode capacitance	$V_R = 0$	C_{tot}			2.5	pF

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

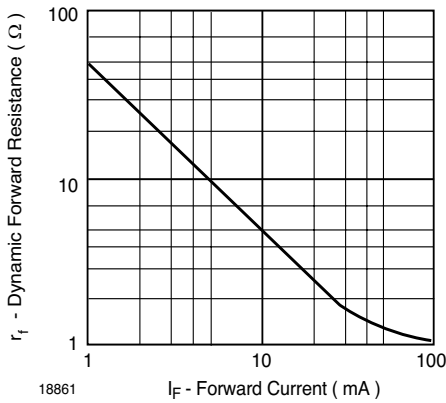


Figure 1. Dynamic Forward Resistance vs. Forward Current

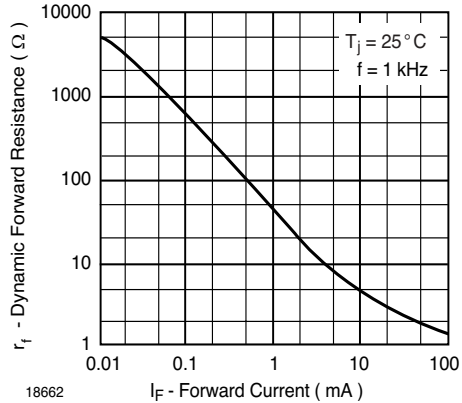


Figure 3. Dynamic Forward Resistance vs. Forward Current

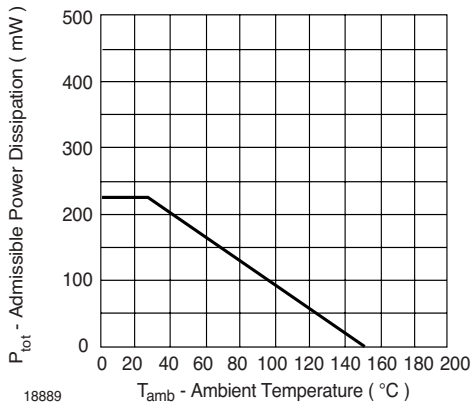


Figure 2. Admissible Power Dissipation vs. Ambient Temperature

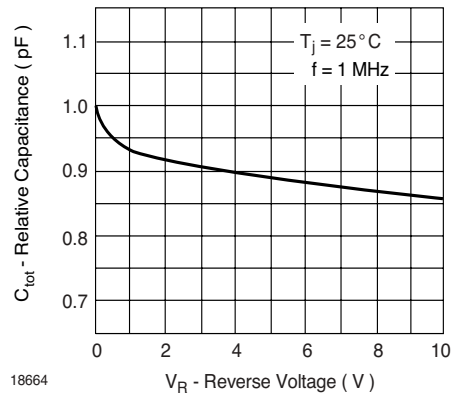


Figure 4. Relative Capacitance vs. Reverse Voltage

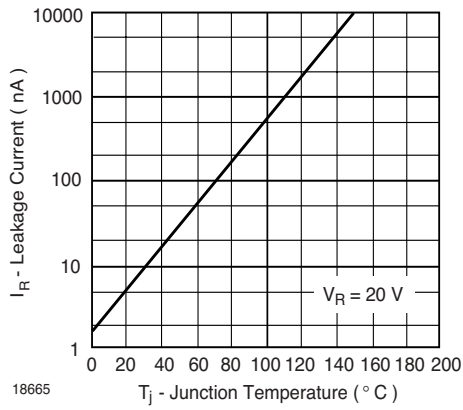


Figure 5. Leakage Current vs. Junction Temperature

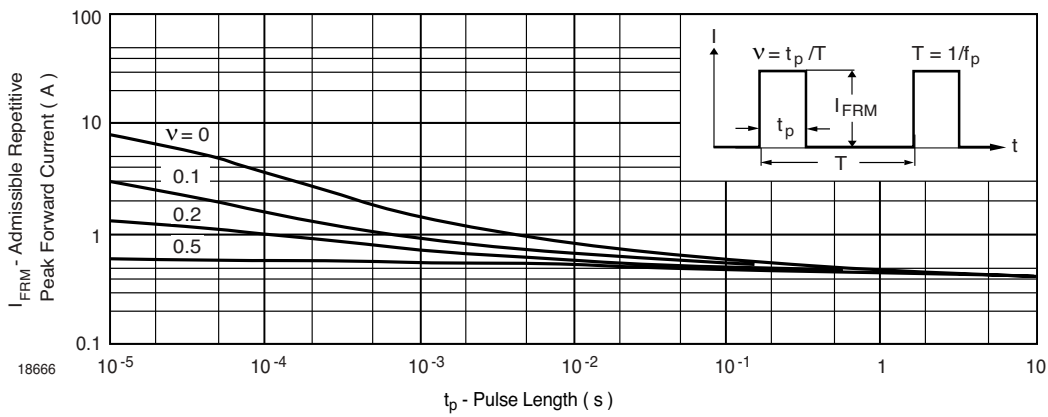


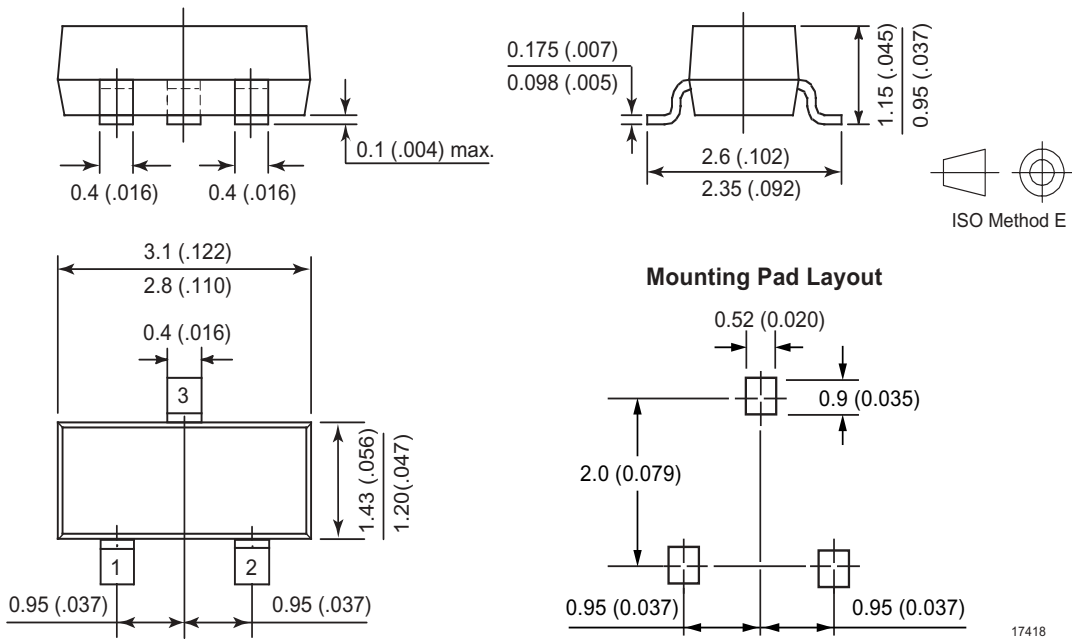
Figure 6. Admissible Repetitive Peak Forward Current vs. Pulse Duration

MMBD6050

Vishay Semiconductors



Package Dimensions in mm (Inches)





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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